

PBSS5360Z

60 V, 3 A PNP low V_{CEsat} (BISS) transistor

19 February 2014

Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4360Z.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

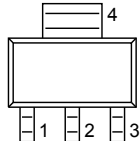
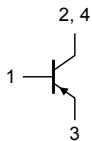
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-60	V
I _C	collector current		-	-	-3	A
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse	-	-	-6	A
R _{CEsat}	collector-emitter saturation resistance	I _C = -2 A; I _B = -200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	225	mΩ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	 <p>SC-73 (SOT223)</p>	 <p>sym028</p>
2	C	collector		
3	E	emitter		
4	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5360Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5360Z	P5360Z

8. Limiting values

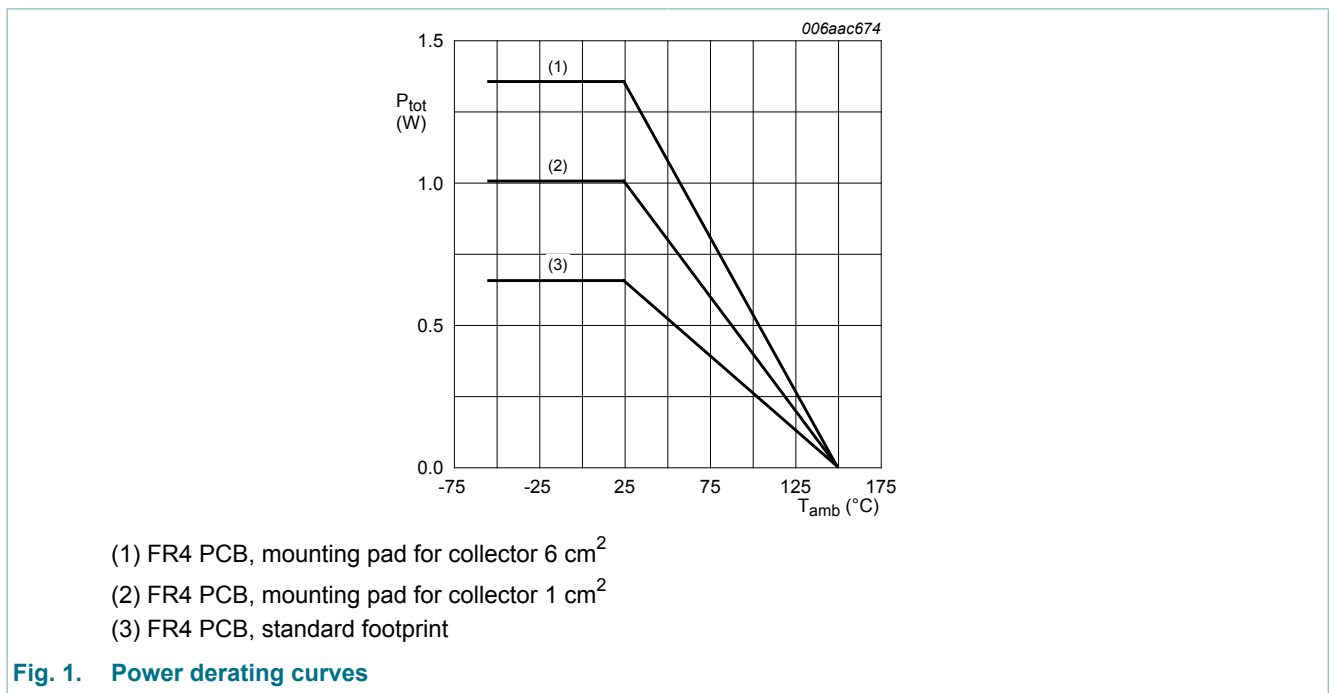
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-80	V
V_{CEO}	collector-emitter voltage	open base	-	-60	V
V_{EBO}	emitter-base voltage	open collector	-	-7	V
I_C	collector current		-	-3	A
I_{CM}	peak collector current	$t_p \leq 1$ ms; single pulse	-	-6	A
I_B	base current		-	-500	mA
I_{BM}	peak base current	$t_p \leq 1$ ms; single pulse	-	-1	A
P_{tot}	total power dissipation	[1]	-	0.65	W
		[2]	-	1	W
		[3]	-	1.35	W

Symbol	Parameter	Conditions		Min	Max	Unit
			[4]	-	2	W
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 70 μm single-sided copper, tin-plated, mounting pad for collector 6 cm².



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	192	K/W
			[2]	-	-	125	K/W
			[3]	-	-	93	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

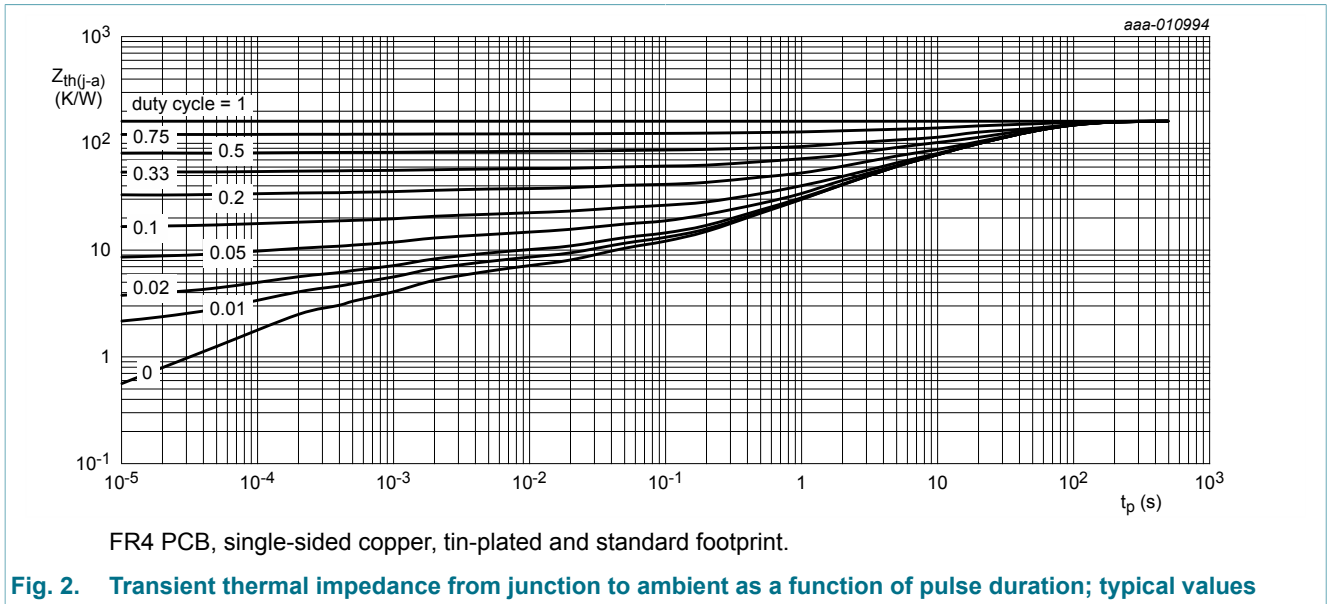
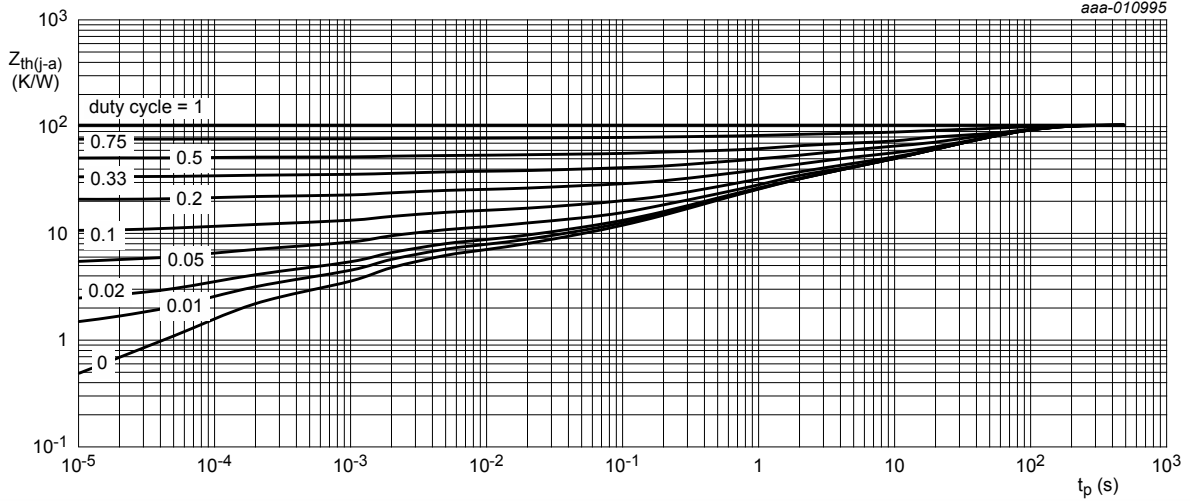
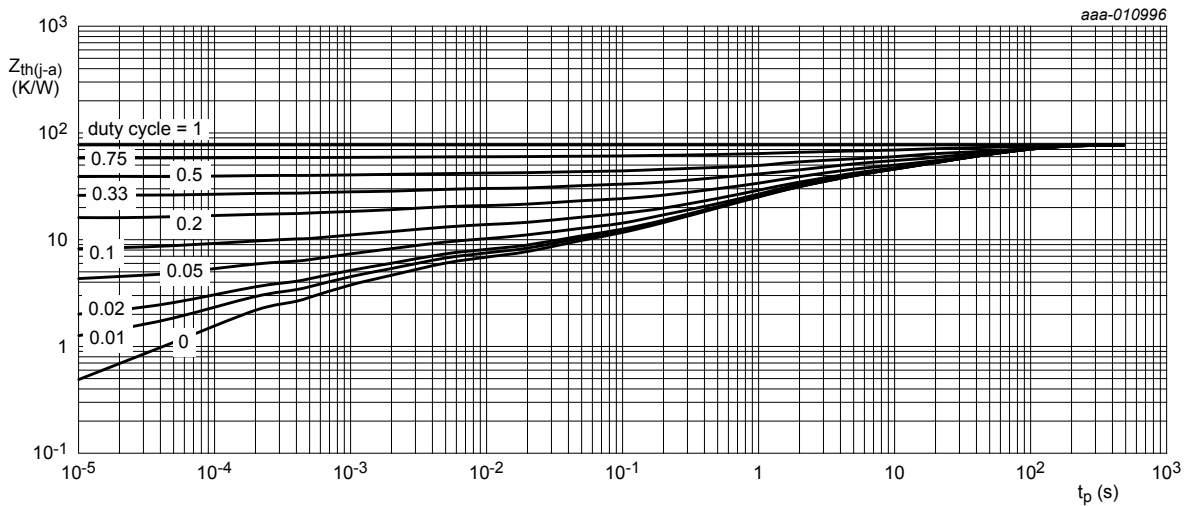


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



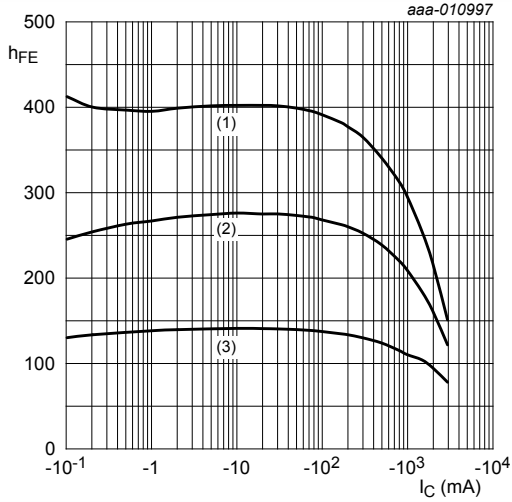
FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

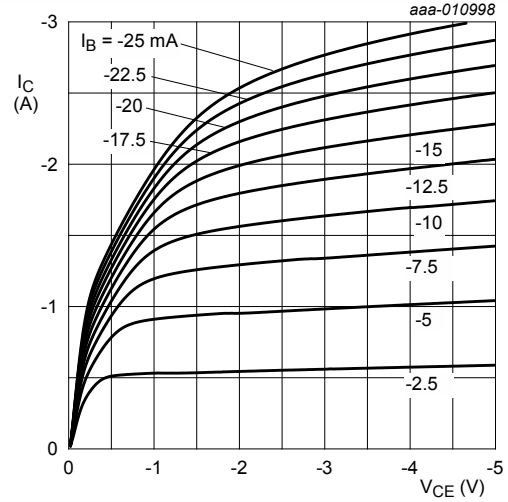
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = -48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
		V _{CB} = -48 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -50 mA; T _{amb} = 25 °C	150	-	-	
		V _{CE} = -5 V; I _C = -500 mA; T _{amb} = 25 °C	130	-	-	
		V _{CE} = -5 V; I _C = -1 A; T _{amb} = 25 °C	120	-	-	
		V _{CE} = -5 V; I _C = -2 A; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed	100	-	-	
		V _{CE} = -5 V; I _C = -3 A; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -500 mA; I _B = -50 mA; T _{amb} = 25 °C	-	-	-150	mV
		I _C = -1 A; I _B = -100 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed	-	-	-200	mV
		I _C = -2 A; I _B = -200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	-450	mV
		I _C = -3 A; I _B = -300 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	-550	mV
R _{CEsat}	collector-emitter saturation resistance	I _C = -2 A; I _B = -200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	225	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = -1 A; I _B = -100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	-1.2	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = -5 V; I _C = -1 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	-1.1	V
f _T	transition frequency	V _{CE} = -10 V; I _C = -50 mA; f = 100 MHz; T _{amb} = 25 °C	65	130	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	28	32	pF



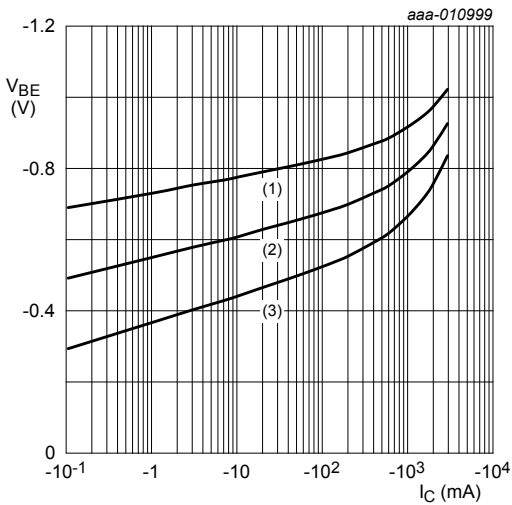
$V_{CE} = -5$ V
 (1) $T_{amb} = 100$ °C
 (2) $T_{amb} = 25$ °C
 (3) $T_{amb} = -55$ °C

Fig. 5. DC current gain as a function of collector current; typical values



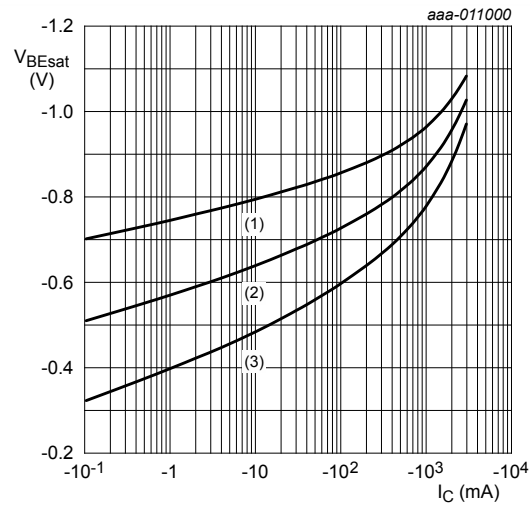
$T_{amb} = 25$ °C

Fig. 6. Collector current as a function of collector-emitter voltage; typical values



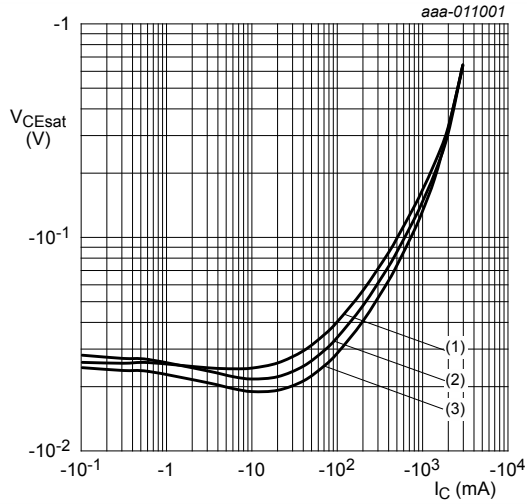
$V_{CE} = -5$ V
 (1) $T_{amb} = -55$ °C
 (2) $T_{amb} = 25$ °C
 (3) $T_{amb} = 100$ °C

Fig. 7. Base-emitter voltage as a function of collector current; typical values



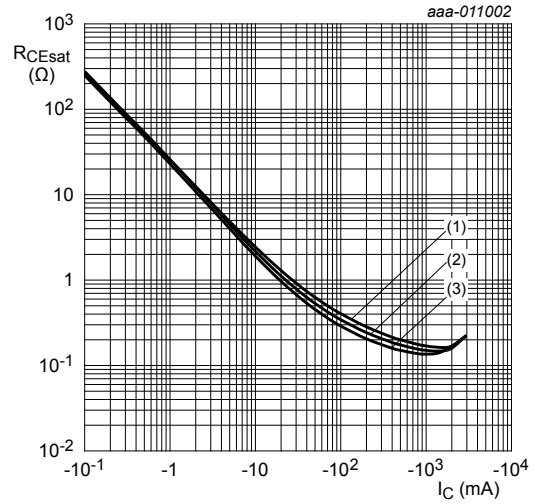
$I_C/I_B = 20$
 (1) $T_{amb} = -55$ °C
 (2) $T_{amb} = 25$ °C
 (3) $T_{amb} = 100$ °C

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

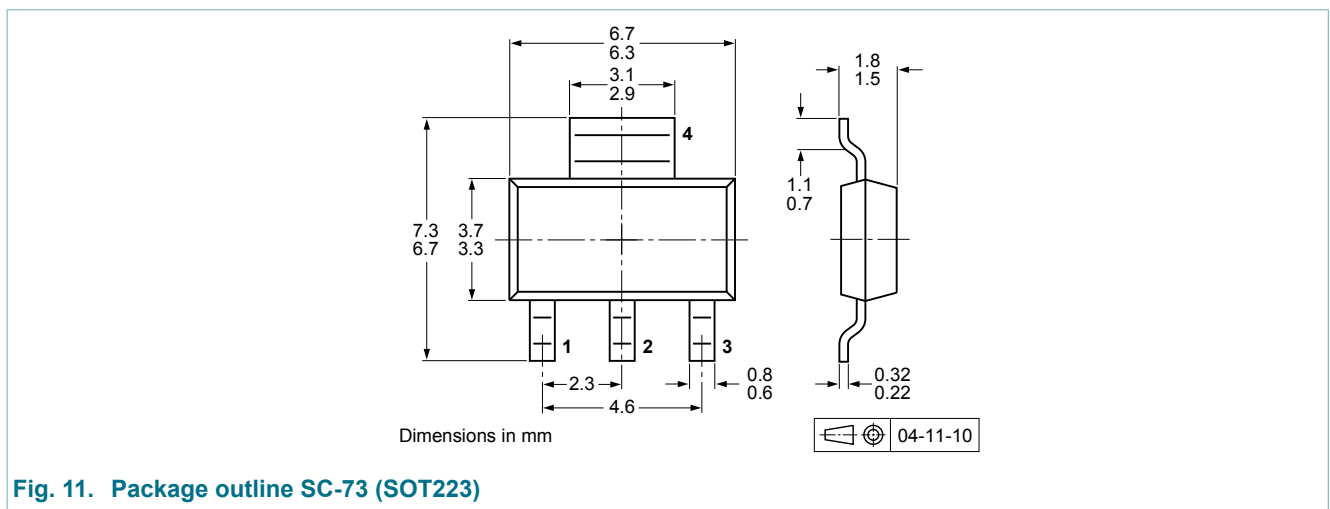
Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



13. Soldering

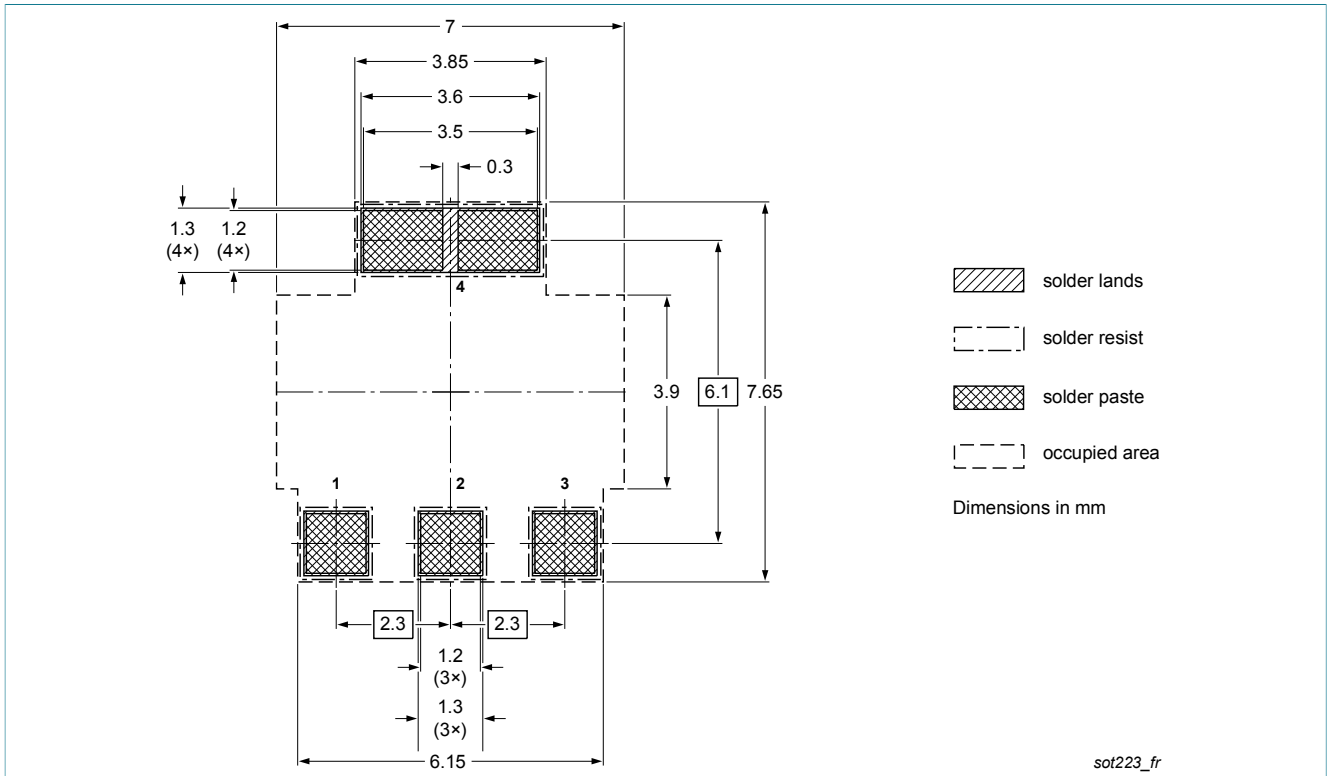


Fig. 12. Reflow soldering footprint for SC-73 (SOT223)

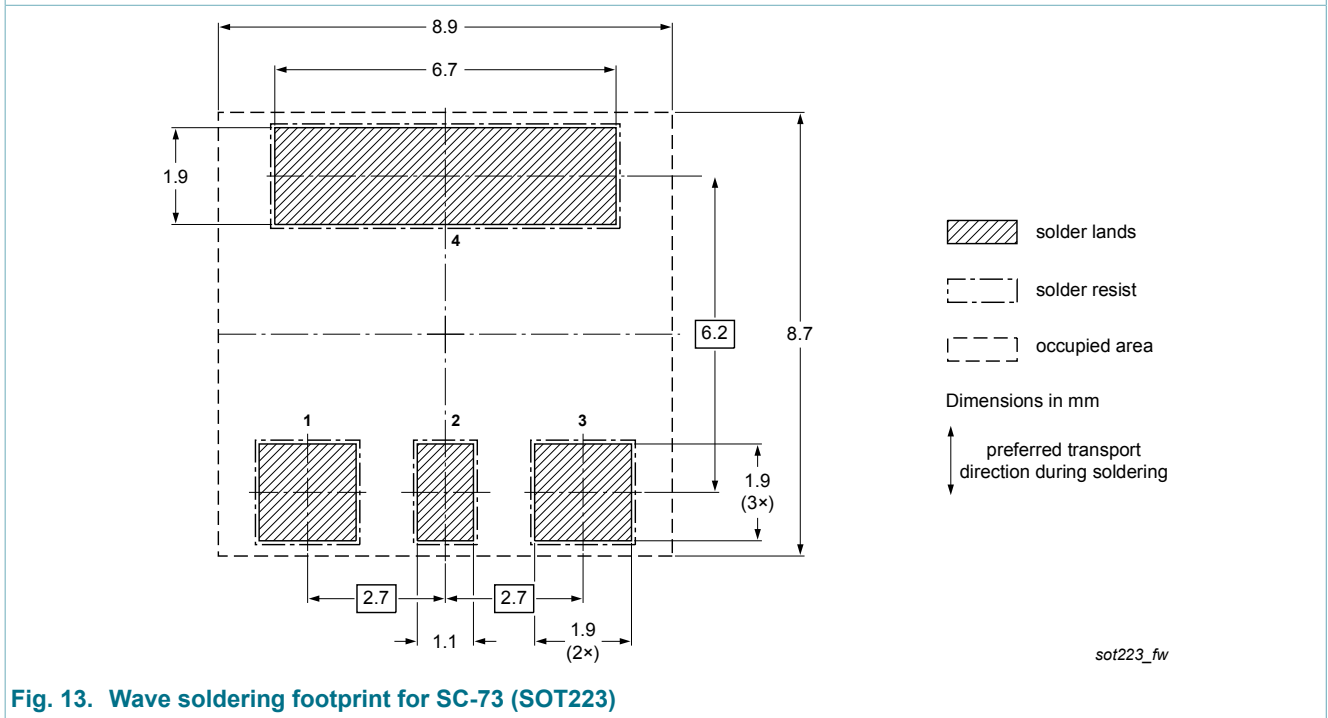


Fig. 13. Wave soldering footprint for SC-73 (SOT223)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5360Z v.1	20140219	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
11.1	Quality information	9
12	Package outline	9
13	Soldering	10
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	13

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